

# Ultrafast and Directional Magnetization Control via Voltage-Controlled Exchange Coupling

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## Abstract

Achieving ultrafast and energy-efficient magnetization switching is essential for next-generation spintronic devices. Voltage-driven switching offers a promising alternative to current-based approaches. Although voltage-controlled exchange coupling (VCEC) has been proposed to steer magnetic states, its ultrafast response and role in polarity selection have not been experimentally verified. Here, we demonstrate that VCEC induces a directional exchange field that persists under nanosecond voltage pulses in a perpendicular magnetic tunnel junction (pMTJ) with an exchange-coupled free layer. This confirms that VCEC can operate on ultrafast timescales and deterministically select the switching polarity. The reversal is primarily assisted by voltage-induced magnetic anisotropy (VCMA), which transiently lowers the energy barrier. This combination enables magnetization switching within 87.5 ps with 50% switching probability and 100 ps with 94% switching probability, respectively. The observed fast switching is enabled in part by enhanced angular momentum dissipation in the exchange-coupled structure, which increases effective damping and accelerates relaxation. These findings reveal a purely voltage-driven and dynamically viable route for fast, directional control of magnetization—positioning VCEC as a key functional mechanism for future spintronic logic and memory technologies.

## Main text

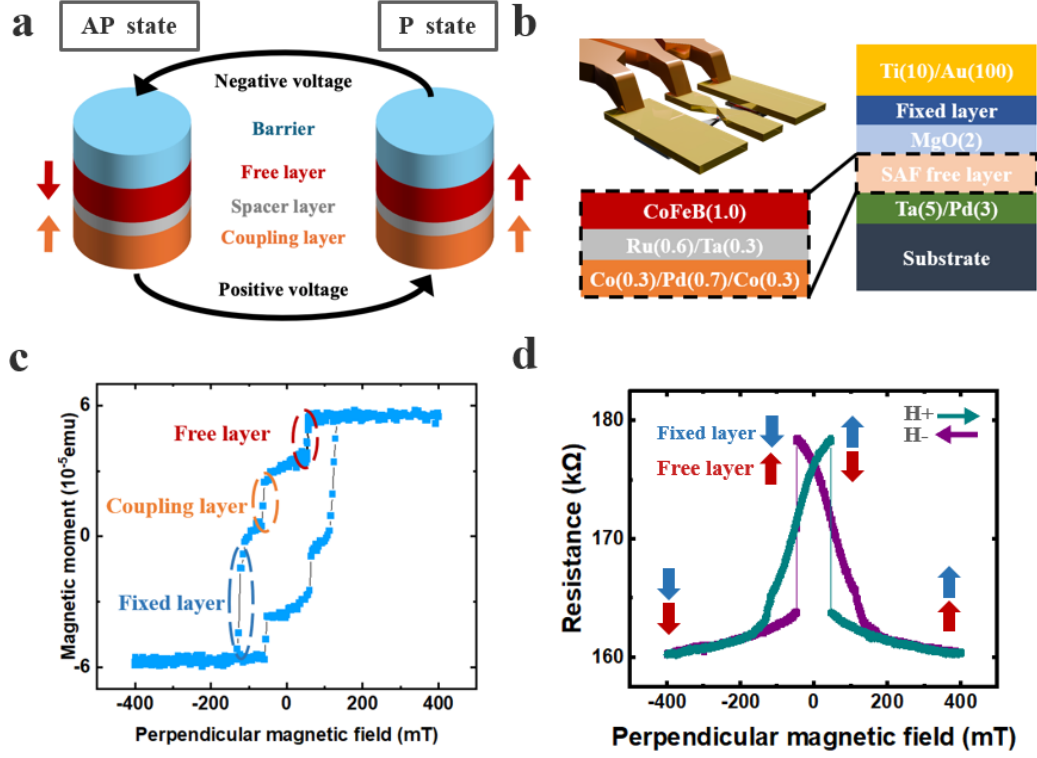
Achieving energy-efficient and high-speed magnetization switching is essential for enabling next-generation spintronic logic and memory technologies<sup>1–4</sup>. Among existing mechanisms, spin transfer torques (STT) switching in magnetic tunnel junctions (MTJs) has been widely used in magnetic random access memory (MRAM)<sup>5–8</sup>. However, STT-based switching faces challenges in reaching sub-nanosecond magnetization switching due to an incubation delay associated with the collinear alignment of reference and free layer magnetization<sup>9–14</sup>. Various strategies, such as introducing non-collinear spin polarizers or double polarizer configurations, have been proposed to enhance the initial torque and reduce the switching time<sup>23</sup>. While these approaches can shorten switching times to below 250 ps, they often suffer from non-deterministic dynamics and still rely on high current densities. Spin-orbit torque (SOT) switching, based on 3-terminal architectures, can achieve sub-nanosecond speeds, but it requires a charge current, a separate write path and often suffers from increased device footprint, higher energy cost, and post-pulse switching dynamics that limit timing precision<sup>20–23</sup>. These challenges have motivated the development of compact, 2-terminal switching schemes that combine speed, determinism, and pure voltage-driven operation.

To overcome the energy and speed limitations of current-driven mechanisms, voltage-controlled switching strategies have attracted growing interest. Among them, voltage-controlled magnetic anisotropy (VCMA) reduces switching energy by modulating interfacial anisotropy but typically requires an external magnetic field or additional current to achieve deterministic bipolar switching<sup>24–30</sup>. An alternative mechanism, voltage-controlled exchange coupling (VCEC), offers a fundamentally different approach by tuning the interlayer exchange interaction between magnetic layers via electric fields, enabling deterministic bipolar switching without large current densities. Magneto-ionic effects first demonstrated voltage-tunable coupling via ionic motion<sup>31,32</sup>, but switching speed can be limited by ion diffusion. In contrast, Bruno<sup>33</sup> theoretically proposed an electronic pathway for controlling exchange coupling via spin-dependent interfacial reflectivity. This mechanism was recently demonstrated in MgO-based systems<sup>34–37</sup>, representing a voltage-driven alternative to STT switching in two-terminal device<sup>38</sup>. However, to date, VCEC has only been demonstrated under quasi-static conditions with constant voltage, leaving its suitability for nanosecond, deterministic switching unexplored.

In this work, we design, deposit, and pattern a multilayer  $\text{FM}_1/\text{NM}/\text{FM}_2/\text{MgO}/\text{FM}_3$  structure. In this configuration,  $\text{FM}_2/\text{MgO}/\text{FM}_3$  forms a pMTJ, while  $\text{FM}_2$  is antiferromagnetically coupled to  $\text{FM}_1$  through the NM spacer, forming a synthetic antiferromagnet (SAF). This architecture allows us to investigate VCEC by monitoring the effective field induced on the free layer ( $\text{FM}_2$ ) under applied voltage. We demonstrate the presence of a VCEC-induced bipolar effective magnetic field and confirm its existence on the nanosecond timescale. Although VCEC is theoretically capable of bipolar switching, we focus on antiparallel-to-parallel (AP $\rightarrow$ P) switching, as strong VCMA suppresses the reverse transition in our device. With the assistance of VCMA, the AP $\rightarrow$ P switching speed reaches as low as 87.5 ps. We

further reveal an inverse relationship between voltage amplitude and pulse width for durations below 1 ns—analogous to the super-threshold regime in STT switching—indicating a voltage-induced precessional switching mechanism. We observe that smaller devices exhibit more efficient switching, which is further supported by macrospin simulations. The simulations indicate that the switching is primarily driven by a voltage-induced damping-like torque. In smaller devices, the coupled layer exhibits a stronger dynamic response, leading to faster energy dissipation in the free layer. This manifests as an effective increase in damping, providing a possible explanation for the improved switching efficiency observed experimentally.

### **Properties of VCEC stack and patterned devices**



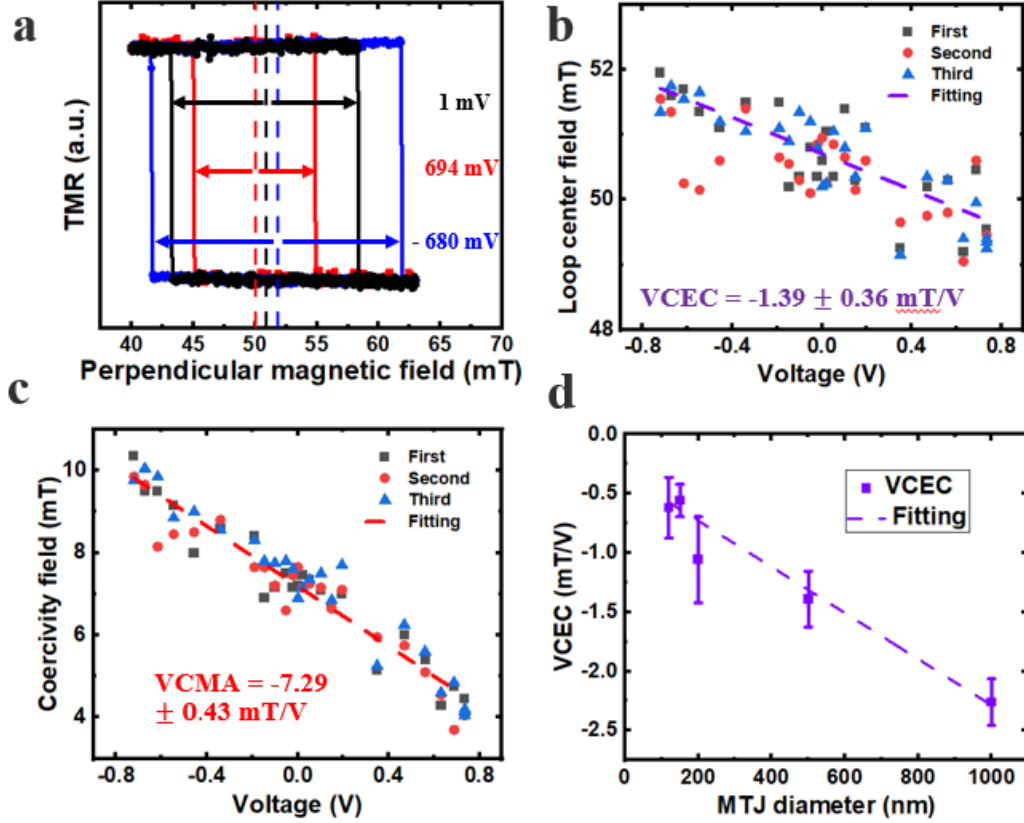
**FIG. 1 | Properties of VCEC stack structure and patterned device.** (a) Schematic illustration of voltage-controlled exchange coupling (VCEC)-induced switching. The free layer is exchange-coupled to the coupling layer via the spacer layer, with the coupling strength modulated by an applied voltage. Under a positive voltage, the AP state is favored, while a negative voltage favors the P state. Due to the free layer's lower coercivity compared to the coupling layer, only the free layer undergoes switching. (b) Schematic of the pMTJ stack structure incorporating an SAF free layer. The fixed layer, positioned above the MgO barrier, detects the free layer's magnetization direction through tunneling magnetoresistance (TMR). The top-right inset shows a patterned device with the top electrode adapted for measurement using a GSG probe. (c) Magnetization vs. perpendicular magnetic field loop of the stack after annealing. The sharp switching transitions indicate the presence of perpendicular magnetic anisotropy (PMA) in the free layer, coupling layer, and fixed layer. (d) Resistance vs. perpendicular magnetic field major loop of a patterned pMTJ device (500 nm diameter). The PMA remains, as evidenced by the distinct resistance states.

Fig. 1(a) illustrates the fundamental structure enabling the VCEC effect. The free and coupling layers, positioned beneath the barrier layer, are exchange-coupled via the spacer layer. Their relative alignment—either AP or P—can be controlled by applying a negative or positive voltage. It is well established that modulating the spacer layer thickness induces oscillatory coupling between the AP and P states<sup>39,40</sup>, a characteristic behavior of the Ruderman-Kittel-Kasuya-Yosida (RKKY) interaction. This effect can be similarly achieved by modifying the electrostatic potential of the barrier layer, shifting the relative energy of the AP and P states and enabling voltage-controlled switching<sup>33,34</sup> (Supplementary Section 1). To investigate the effect, we deposited a multilayer stack on a SiO<sub>2</sub> substrate with the structure: Substrate/Ta(5)/Pd(3)/Co(0.3)/Pd(0.7)/Co(0.3)/Ru(0.6)/Ta(0.3)/CoFeB(1)/MgO(2.0)/CoFeB(

1.3)/Ta(0.7)/[Pd(0.7)/Co(0.3)]<sub>4</sub>/Pd(5) (unit in nm). The core structure, illustrated in Fig. 1(b), consists of: (1) Fixed layer: CoFeB(1.3)/Ta(0.7)/[Pd(0.7)/Co(0.3)]<sub>4</sub>, providing a stable reference magnetization; (2) Free layer: CoFeB(1), positioned beneath the MgO barrier, whose magnetization is tunable via voltage; (3) Coupling layer: Co(0.3)/Pd(0.7)/Co(0.3), generating the interlayer exchange coupling field; (4) Spacer layer: Ru/Ta, mediating the interlayer exchange coupling between the free and coupling layers. A relatively thick MgO barrier (2 nm) was chosen to minimize current-driven effects while enabling the application of higher voltage.

After rapid thermal annealing, the perpendicular anisotropy of the stack was confirmed via out-of-plane M-H loop measurements (Fig. 1(c)). The three-step magnetization reversal process, occurring from +400 mT to -400 mT, corresponds to the sequential switching of the free layer, coupling layer, and fixed layer. The opposite signs of the free and coupling layers' switching field indicate antiferromagnetic (AF) exchange coupling at zero magnetic field. Patterned nanoscale pillars of various diameters (100–2000 nm) were fabricated via photolithography and electron-beam lithography (Methods). An oblique view of the patterned device is shown in the top-right corner of Fig. 1(b). To facilitate high-frequency electrical excitation, a specially designed electrode pattern was implemented to minimize overlap between the top and bottom electrodes, enabling efficient GHz frequency pulse injection into the MTJ pillar via a ground-signal-ground (GSG) probe. Fig. 1(d) presents the resistance-field (R-H) loop of a 500 nm device, revealing distinct resistance states corresponding to different magnetization alignments. The measured tunneling magnetoresistance (TMR) ratio is ~11%, with a resistance-area (RA) product of  $3.93 \times 10^4 \Omega \cdot \mu m^2$ . A size-dependent resistance analysis, presented in the Extended Data Fig. 1(b), aligns well with theoretical expectations.

## VCMA and VCEC induced effective magnetic field

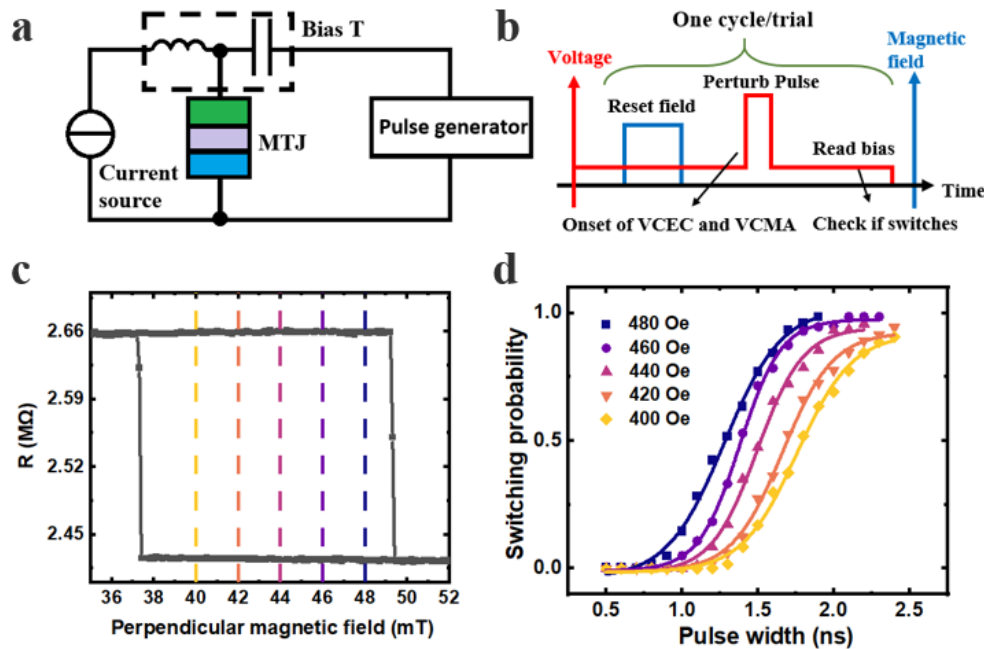


**FIG. 2 | VCEC and VCMA induced effective magnetic field.** (a) Normalized minor loops of a 500 nm MTJ under different applied voltages. A positive (negative) voltage reduces (increases) the loop width due to VCMA and shifts the loop leftward (rightward) due to VCEC. (b) Loop center field and (c) coercivity of the minor loops as functions of the applied voltage. Three loops per voltage are collected to minimize errors. VCEC and VCMA are extracted from the slopes of the linear fits. (d) Extracted VCEC strength in MTJ pillars of different diameters. Error bars represent uncertainties from the linear fitting process.

Fig 2(a) shows normalized electrical minor loops of the 500 nm device under different voltages. Before measurement, a large magnetic field was applied to saturate magnetization in the positive direction, ensuring that in the AP state, only the free layer's magnetization is reversed. A constant current was used for resistance measurements, and the average voltage between AP and P states was recorded. Under an applied voltage, two effects are observed: VCMA and VCEC. The VCMA effect alters anisotropy, manifesting as changes in coercivity. A positive voltage increases anisotropy, leading to a wider loop, consistent with prior VCMA studies, where electron depletion enhances the free layer anisotropy<sup>24,25</sup>. On the other hand, VCEC shifts the minor loop center due to modulation of the exchange coupling field. The loop shifts left or right, depending on voltage polarity. Loop center field and coercivity measurements, averaged over three trials per voltage, exhibit linear voltage dependence (Fig. 2(b-c)). The extracted VCEC and VCMA strengths are  $-1.39 \pm 0.36 \text{ mT}$  and  $-7.29 \pm 0.43 \text{ mT}$ , respectively.

The significantly smaller VCEC value compared to VCMA limits the feasibility of bipolar switching in our devices (Supplementary Section 2). The reduced VCEC strength may result from limited interlayer coupling or non-uniform voltage distribution in the current device structure. Further enhancement could be realized by optimizing the spacer layer and improving the crystalline quality of the MgO barrier. Notably, the observed loop shift cannot be attributed to STT, as: (1) it exhibits a linear dependence on the applied voltage, and (2) in STT-driven switching, a positive current favors the AP state, contradicting the observed behavior. Fig. 2(d) shows that VCEC strength scales approximately linearly with MTJ diameter, with smaller devices exhibiting weaker effects. This trend likely arises from pillar boundary effects, where the intact central area is proportional to  $S/D \sim d$ , where  $S$  is the pillar area,  $D$  is the perimeter, and  $d$  is the diameter. The VCMA strength, expressed as the effective field per volt, does not exhibit a clear trend with size due to the variability in coercivity (Supplementary Section 2).

### Rapid Speed of the VCEC Effect

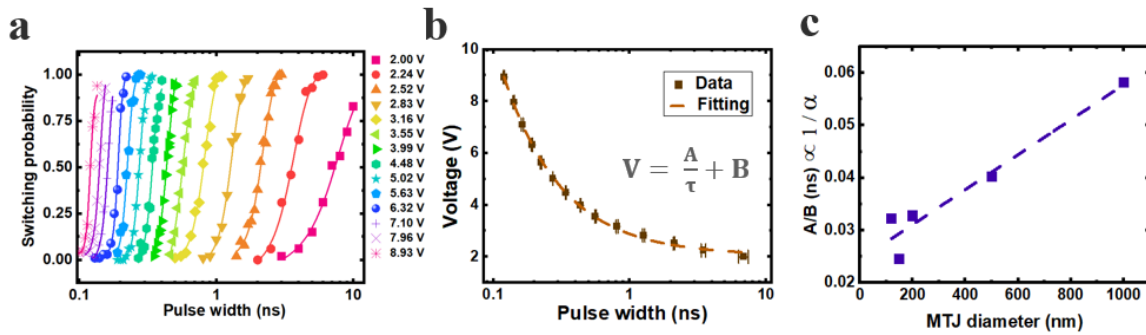


**FIG. 3 | VCEC and VCMA induced effective magnetic field.** (a) Schematic of the ultrafast pulse switching test setup. The pulse generator applies voltage pulses to the MTJ, while the current source reads out the MTJ state using a small DC current. (b) Test sequence for switching probability evaluation. The MTJ is first reset to the AP state using an external magnetic field. A perturbation voltage pulse from the pulse generator induces VCMA and VCEC effects in the MTJ. A small constant current is applied continuously to monitor the MTJ state after each perturbation. (c) Minor loop of the 150 nm MTJ. The reference line indicates the applied external magnetic field used in the subsequent fast switching test. (d) Switching probability as a function of pulse width, with the pulse amplitude fixed at 3.56 V.

To investigate the response of the pMTJ under an ultrafast pulse, we implemented the circuit in Fig. 3(a). DC bias current of 5 nA was applied via the DC port of bias T to continuously monitor resistance after each pulse, while ultrafast pulses were injected through the AC port.

Since the MTJ resistance is significantly higher than  $50\ \Omega$ , the actual pulse amplitude at the MTJ was approximately doubled, following:  $\Gamma(R)=2Z_0/(Z_0+R)$ , where  $R=50\ \Omega$  and  $Z_0$  is dominated by the MTJ impedance, which is much higher than  $50\ \Omega$ . Fig. 3(b) illustrates the testing sequence. Initially, a 1 mT magnetic field sets the MTJ to the AP state. The field is then adjusted within the bistable region, and a voltage pulse with varying width/amplitude is applied. Post-pulse resistance is measured to determine switching. Each probability data point in Fig. 3(d) is averaged over 200 trials. Fig. 3(c) presents the minor loop of a 150 nm device. A device with relatively larger coercivity is selected to investigate the effect of an applied magnetic field on switching. Magnetic fields ranging from 40 to 48 mT, within the bipolar state region, are chosen. The voltage amplitude remains fixed at 3.56 V, while the pulse width is gradually increased from 0.5 ns until the switching probability reaches approximately 0.95. The sigmoid-fit results in Fig. 3(d) indicate that a magnetic field near the AP-to-P threshold accelerates switching, attributed to a reduced effective energy barrier. The observed switching stems from a combination of the external field, VCMA, and potentially VCEC. In a device governed solely by the VCMA effect, the minor loop contracts toward the center under a positive voltage, AP-to-P switching occurs only if the external field exceeds the loop center field. If the external field is below this threshold, switching is suppressed, as the field favors the AP state. However, the observed switching at 40 and 42 mT suggests the presence of an additional effect that counteracts the external field and facilitates switching. These findings confirm the persistence of the VCEC effect on the nanosecond timescale, eliminating the slower VCEC mechanism associated with ion drifting in our stack. This highlights VCEC's potential as a viable replacement for STT, even in the GHz regime.

### Voltage dependent switching speed and its size dependency



**FIG. 4 | Fast switching results under different applied voltages.** (a) Switching probability as a function of pulse width under different applied voltages. As the voltage increases from 2.00 V to 8.93 V, the switching probability increases with pulse width. (b) Voltage and pulse width corresponding to the 50% switching probability points. The pulse width is inversely proportional to the applied voltage as is fitted by the equation inset. (c) Fitted parameters  $A/B$  across various device sizes. Since  $A/B$  is inversely proportional to the effective damping constant in the single-domain model, we conclude that the effective damping increases as the MTJ size decreases.



We investigate the impact of voltage amplitude on switching under a fixed magnetic field (Methods). Fig. 4(a) illustrates the switching probability as a function of pulse width across multiple voltage levels for a 500 nm device, with all curves well-fitted by a sigmoid function. The switching behavior is deterministic, with the probability approaching 1 as the pulse width increases. Higher voltage amplitudes reduce the required pulse width for a given switching probability. Notably, the device remains switchable even at the minimum pulse width supported by the pulse generator (0.1 ns, generator 1 in Method). To further explore the switching speed limit, we employed a shorter pulse generator (generator 2 in Method) with fixed output of 5 V (yielding 10 V across the MTJ). This setup achieved a switching time of 87.5 ps (Extended Data Fig. 2(a)), with a rise time of 40 ps, highlighting an exceptionally short incubation time.

The pulse width corresponding to 50% switching probability is extracted and plotted as a function of voltage in Fig. 4(b). The data is well-described by:

$$V = \frac{A}{\tau} + B, \quad (1)$$

where  $V$  represents the voltage and  $\tau$  denotes the pulse width and  $A$ ,  $B$  are fitting parameters. Similar trends are observed across different device sizes (Extended Data Fig. 3(a)). This relationship resembles the super-threshold STT regime, indicating a precessional switching mechanism<sup>41,42</sup>. Following a similar derivation in the STT case, we derive an analogous expression for voltage-induced torque based on the single-domain model, yielding the following equations (Supplementary Section 3):

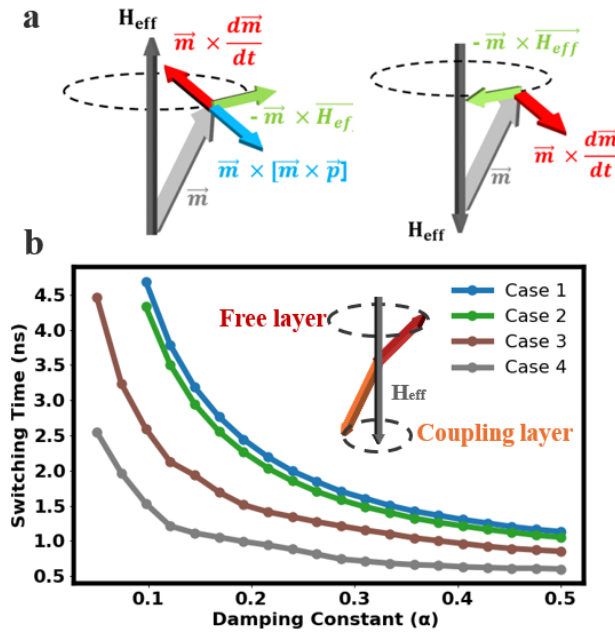
$$A = \frac{\left(\frac{1 + \alpha^2}{\alpha\gamma\mu_0}\right) \cdot \ln\left(\frac{\pi}{2\theta_0}\right)}{|a + b|}, \quad (2)$$

$$B = \frac{H_k - H_{\text{ext}}}{|a + b|}, \quad (3)$$

where  $B$  is equivalent to the critical voltage,  $a$  and  $b$  are VCEC and VCMA coefficient, respectively, represented by the effective field per volt,  $\alpha$  is the damping constant,  $\gamma$  is the gyromagnetic ratio,  $\mu_0$  is the vacuum permeability,  $\theta_0$  is the initial angle of magnetization from easy axis,  $H_k$  is the effective anisotropy field, and  $H_{\text{ext}}$  is the applied magnetic field measured relative to the loop center field. We define the numerator on the right-hand side of equation (2) and (3) as  $A'$  and  $B'$ . The relationships  $A'$  and  $B'$  as a function of device size are plotted in Extended Data Fig. 3. In these terms, the size contributions of VCMA and VCEC are accounted for, ensuring they do not affect the observed variations.  $A'$  generally exhibits an increasing trend with device size, accompanied by minor fluctuations, while  $B'$  remains nearly constant with similar variations. According to equation (3), although  $H_k$  is supposed to be the same for all the devices,  $B'$  depends on the manually selected applied field (Method), contributing to the variance. Since similar fluctuations are observed in  $A'$ –

size relationship, this suggests that variations in  $B'$  also impact  $A'$  by modifying  $\theta_0$ , as described by:  $A' \propto \frac{1}{\theta_0} \propto H_k - H_{\text{ext}} \propto B'$ . To account for these variations,  $A'/B'$  is plotted as a function of MTJ size in Fig. 4(d). The ratio  $A'/B'$  increases with the increasing device size, suggesting more efficient switching at smaller size device. Notably from equation (2) and (3),  $\frac{A'}{B'} = \frac{A}{B} \propto \left(\frac{1+\alpha^2}{\alpha}\right)$ . For damping values much smaller than 1, this simplifies to  $\propto 1/\alpha$ . The observed trend indicates that smaller devices exhibit a higher effective damping constant in the single domain model.

### Faster switching speed benefits from the larger effective damping



**FIG. 5 | Illustration of the torque direction and the simulation result.** (a) (left): Torque orientation in STT-induced switching. The anti-damping-like torque must overcome the damping-like torque to induce switching. (a) (right): Torque orientation in voltage-induced switching. The effective field reverses, as does the damping-like torque. The torque drives the local magnetic moment toward the new  $H_{\text{eff}}$  direction to minimize energy. (b) Simulation results showing switching time as a function of the damping constant. Four cases are considered: Case 1: A single free layer. Case 2-4: A coupled system where the free layer interacts with the coupling layer. Specifically, Case 2:  $H_{\text{CP}}=50$  mT,  $H_{\text{k2}}=500$  mT, Case 3:  $H_{\text{CP}}=25$  mT,  $H_{\text{k2}}=50$  mT, Case 4:  $H_{\text{CP}}=50$  mT,  $H_{\text{k2}}=50$  mT. In all cases, a higher damping constant results in shorter switching times. The introduction of coupling accelerates switching, and the trajectory of the coupling layer further influences the magnitude of this effect.

Fig. 5(a) illustrates the torque directions for STT switching and voltage-induced effective field switching. In STT switching (Fig. 5(a), left), the spin current primarily exerts torque on the local magnetization through the anti-damping-like torque (along  $\vec{m} \times \vec{m} \times \vec{p}$ ). Switching occurs only if this torque overcomes the damping-like torque (along  $\vec{m} \times \frac{d\vec{m}}{dt}$ ), which acts like friction. To enhance switching efficiency and speed, significant efforts are needed to reduce the damping constant of the ferromagnetic layer. However, the switching mechanism changed in voltage-induced switching (Fig. 5(a), right). Here, the applied voltage reverses the sign of the effective field ( $\vec{H}_{\text{eff}}$ ), causing the magnetization to precess around the new  $\vec{H}_{\text{eff}}$ . In this case, the accompanying damping-like torque (along  $\vec{m} \times \frac{d\vec{m}}{dt}$ ) acts as the driving force for switching. As a result, a larger damping constant becomes desirable for faster switching. To validate this concept, a macromagnetic simulation was performed to examine the effect of damping on switching speed. The simulation models the case of  $V = 4$  V for a 500 nm device (Supplementary Section 5). The switching trajectory of the free layer's normalized magnetic moment under selected damping constants is shown in (Extended Data Fig. 4, Case1), and the corresponding switching times are plotted in Fig. 5(b). The results indicate that the switching speed increases with increasing  $\alpha$  ( $\alpha < 1$ ). However, achieving sub-ns switching at the same voltage, as observed in the experiment, would require an exceptionally high damping constant. Moreover, the size-dependent variation in  $\alpha$  is unexpected (Fig. 4(c)), as all devices, regardless of size, should share the same intrinsic  $\alpha$  value, given that they are patterned from the same material stack.

We note that effective damping can be influenced by the movement of the coupling layer's magnetization, which is triggered by the onset of exchange coupling. This motion, in turn, affects the switching efficiency in our stack. Ideally, the coupling layer should remain fully fixed during the free layer's switching process. In this scenario, the strength of the exchange coupling would not influence the damping constant, similar to a single-spin case. However, since the easy axis of the coupling layer is along the z-direction, an in-plane component of the effective exchange coupling field can induce a slight tilt in the coupling layer, causing it to rotate in the in-plane direction along with the free layer during the switching. This out-of-phase rotation introduces an additional source of spin momentum dissipation, effectively increasing the damping constant of the free layer. To account for this effect, we incorporate additional cases into the simulation. In Case 2, we set  $H_{\text{CP}}=50$  mT,  $H_{k2}=500$  mT (where  $H_{k2}$  is intentionally set to an unrealistically high value). Here,  $H_{\text{CP}}$  and  $H_{k2}$  represent the interlayer exchange coupling field and the effective anisotropy field of the coupling layer, respectively. By comparing Case 1 and Case 2, we observe that even a slight tilt in the coupling layer's magnetization angle during the switching leads to a significant ( $\sim 10\%$ ) reduction in switching time when exchange coupling is present. In Case 4, where  $H_{\text{CP}} = 50$  mT and  $H_{k2} = 50$  mT ( $H_{k2}$  closely matching the experimental value), the switching speed is further enhanced. To isolate the contribution of the exchange coupling field, we reduce  $H_{\text{CP}}$  to 25 mT while keeping  $H_{k2} = 50$  mT in Case 3. This results in a slower switching speed compared to Case 4, but it remains faster than Case 1, where  $H_{\text{CP}} = 0$  mT. As shown in Extended Data Fig. 4(a, b), the deviation

of the coupling layer from the out-of-plane direction increases progressively from Case 1 to Case 4, indicating that greater deviation of the coupling layer contributes to faster switching. In our simulation, we only consider coupled magnetization dynamics; however, additional effects, such as spin pumping, could further contribute to the damping enhancement<sup>43–45</sup>. Overall, a larger  $H_{CP}$  and a smaller  $H_{k2}$  facilitate faster switching by increase the deviation of the coupling layer during the free layer switching.

In our devices, smaller-sized MTJs exhibit lower stability, as MTJ stability is proportional to its volume and thus scales with the square of the diameter. This reduced stability of the coupling layer thus contributes to the observed faster switching. Meanwhile, we note that the  $H_{CP}$  is not strictly constant. In an SAF structure, the coupling strength between the two layers varies with pillar size, primarily due to changes in the dipole field<sup>46</sup>. The plot of loop center field versus  $1/\text{diameter}$  (Extended Data Fig. 1(c)) confirms that as the pillar size changes, the increased dipole field interacts with the interlayer exchange coupling, thereby modifying the overall coupling strength. Although this effect suggests that larger devices should switch faster, the size-dependent stability effect dominates. In the ideal scenario, where the VCEC-induced effective field is sufficiently strong to enable bipolar switching, the coupling strength will always increase during switching, leading to an enhanced damping effect and, consequently, faster switching.

## **Conclusions**

In summary, we have demonstrated that VCEC enables ultrafast and directional magnetization control in pMTJs. Using nanosecond-scale voltage pulses, we observed the persistence of a directional exchange field under sub-nanosecond conditions, confirming the fast response of VCEC. These results provide experimental evidence that exchange coupling can be modulated electronically besides ionically, fundamentally distinguishing the VCEC mechanism from magneto-ionic approaches that rely on ionic diffusion. By combining this effect with VCMA, we achieved deterministic magnetization switching within 87.5 ps. Macrospin simulations reveal that the torque responsible for voltage-driven switching is field-like, in contrast to the damping-like torques in STT or SOT mechanisms. This field-like torque benefits from enhanced angular momentum dissipation through exchange coupling, leading to faster relaxation and switching dynamics. These effects were further amplified in smaller devices and might be further enhanced in SAF structures with stronger interlayer coupling. Together, these results establish VCEC as a voltage-driven mechanism capable of fast, deterministic, and energy-efficient switching. Looking forward, further engineering of the device architecture may lead to even faster and more robust operation, shedding light on a pathway toward high-speed, low-power spintronic memory and logic applications.

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## **Methods**

### **Device Fabrication and Film Growth**

The pMTJ stack was deposited on a thermally oxidized Si substrate at room temperature using DC and RF magnetron sputtering in the Shamrock system. The base pressure during deposition was maintained at  $< 5 \times 10^{-8}$  Torr. The layer structure of the fabricated stack is as follows (thicknesses in nm): Ta(5) / Pd(3) / Co(0.3) / Pd(0.7) / Co(0.3) / Ru(0.6) / Ta(0.3) / CoFeB(1) / MgO(2.0) / CoFeB(1.3) / Ta(0.7) / [Pd(0.7) / Co(0.3)]<sub>4</sub> / Pd(5). RTP-600S Rapid Thermal Processing System was used for the rapid thermal annealing (RTA) with the temperature of 350°C for 20 min to develop perpendicular magnetic anisotropy (PMA). The magnetic properties of the film stacks were characterized using a vibrating sample magnetometer (VSM) in a Dynacool chamber (Quantum Design). Thin films were patterned into circularly shaped MTJ devices with diameters of 100, 120, 150, 200, 500, 1000, and 2000 nm using electron-beam lithography (EBL) and argon (Ar) ion-beam milling. The electrical size of the devices was validated through the size dependent resistance. The extracted large resistance-area (RA) product of around  $3.93 \times 10^4 \Omega \cdot \mu\text{m}^2$  showed good agreement with the thick MgO thickness of 2 nm.

## **Electrical Measurements**

DC electrical measurements were performed using a Keithley 2400 multimeter. Resistance-field (R-H) loops and minor loops were measured at varying applied currents. The currents are converted to the average voltage between AP and P states for voltage effect evaluation. To investigate the response time of VCEC-induced switching, we applied ultrafast voltage pulses to the MTJ using two pulse generators. The setup included a bias-tee circuit to enable simultaneous DC bias application and high-speed pulse injection (Fig. 3(a)). Model 5541A Bias Tee (80 kHz – 26 GHz, 8 ps rise time) was used. Generator 1: Picosecond Pulse Labs Pulse Generator 10,060A with the pulse width: 100 ps–10 ns, output voltage: 10 V, max rise time: 55 ps. Generator 2: Alnair Labs Electrical Pulse Generator (EPG-210B-0300-S-P-T-A) with the pulse width: 30 ps – 230 ps, output voltage: 5 V, rise time: 40 ps. All the switching results except for those shown in Extended Data Fig. 2 are collected by Generator 1. The output pulses profiles are collected by Tektronix DPO72004B digital phosphor oscilloscope with the bandwidth of up to 20 GHz.

For measurement with fixed magnetic field, the external field was fixed near the AP-to-P switching threshold but remained stable enough to prevent spontaneous switching. Each minor loop measurement was repeated 100 times (2 Oe/s) per device to precisely extract the AP-to-P switching field. A field with zero spontaneous switching probability was chosen to ensure that all observed switching was induced by the applied voltage pulse rather than thermal agitation. Switching probability is calculated based on 100 trials for those tests.

## **Data availability**

Data are available from the corresponding authors upon request.

## **Code availability**

The codes used for the macrospin simulations are available from the corresponding authors upon request.

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### **Author contributions**

Q.J. and J.P. designed the experiments. J.P. led and coordinated the research. D.Z. deposited the films. Q.J., B.D., and D.L. performed the annealing. Q.J., Y.C.C., and O.B. fabricated the samples. Q.J. and S.L. conducted the DC electrical and magnetic measurements. Q.J., Y.L., and B.Z. performed the MTJ fast switching test. Q.J. carried out the micromagnetic simulation. Q.J., Y.Y. analyzed the results. Q.J. drafted the manuscript with input from all authors.

### **Competing interests**

The authors declare no competing interests.

### **Additional information**

#### **Extended data**

#### **Supplementary information**